

BC846ALT1G Series

General Purpose Transistors

NPN Silicon

Features

- Moisture Sensitivity Level: 1
- ESD Rating – Human Body Model: >4000 V
– Machine Model: >400 V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC846 BC847, BC850 BC848, BC849	V_{CEO}	65 45 30	Vdc
Collector-Base Voltage BC846 BC847, BC850 BC848, BC849	V_{CBO}	80 50 30	Vdc
Emitter-Base Voltage BC846 BC847, BC850 BC848, BC849	V_{EBO}	6.0 6.0 5.0	Vdc
Collector Current – Continuous	I_C	100	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

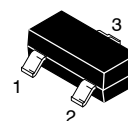
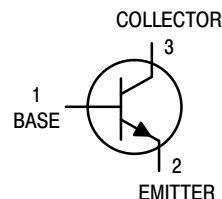
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

- FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.



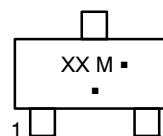
ON Semiconductor®

<http://onsemi.com>



SOT-23
CASE 318
STYLE 6

MARKING DIAGRAM



XX = Device Code
M = Date Code*
■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

BC846ALT1G Series

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = 10 mA)	BC846A,B BC847A,B,C, BC850B,C BC848A,B,C, BC849B,C	V _{(BR)CEO}	65 45 30	– – –	V
Collector – Emitter Breakdown Voltage (I _C = 10 μA, V _{EB} = 0)	BC846A,B BC847A,B,C BC850B,C BC848A,B,C, BC849B,C	V _{(BR)CES}	80 50 30	– – –	V
Collector – Base Breakdown Voltage (I _C = 10 μA)	BC846A,B BC847A,B,C, BC850B,C BC848A,B,C, BC849B,C	V _{(BR)CBO}	80 50 30	– – –	V
Emitter – Base Breakdown Voltage (I _E = 1.0 μA)	BC846A,B BC847A,B,C, BC850B,C BC848A,B,C, BC849B,C	V _{(BR)EBO}	6.0 6.0 5.0	– – –	V
Collector Cutoff Current (V _{CB} = 30 V) (V _{CB} = 30 V, T _A = 150°C)		I _{CBO}	– –	– –	15 5.0 nA μA
ON CHARACTERISTICS					
DC Current Gain (I _C = 10 μA, V _{CE} = 5.0 V)	BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC847C, BC848C	h _{FE}	– – –	90 150 270	– – –
(I _C = 2.0 mA, V _{CE} = 5.0 V)	BC846A, BC847A, BC848A BC846B, BC847B, BC848B, BC849B, BC850B BC847C, BC848C, BC849C, BC850C		110 200 420	180 290 520	220 450 800
Collector – Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA)		V _{CE(sat)}	– –	– –	0.25 0.6 V
Base – Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA)		V _{BE(sat)}	– –	0.7 0.9	– – V
Base – Emitter Voltage (I _C = 2.0 mA, V _{CE} = 5.0 V) (I _C = 10 mA, V _{CE} = 5.0 V)		V _{BE(on)}	580 –	660 –	700 770 mV
SMALL – SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 Vdc, f = 100 MHz)		f _T	100	–	– MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)		C _{obo}	–	–	4.5 pF
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 Vdc, R _S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	BC846A,B, BC847A,B,C, BC848A,B,C BC849B,C, BC850B,C	NF	– –	– –	10 4.0 dB

BC846ALT1G Series

BC846A, BC847A, BC848A

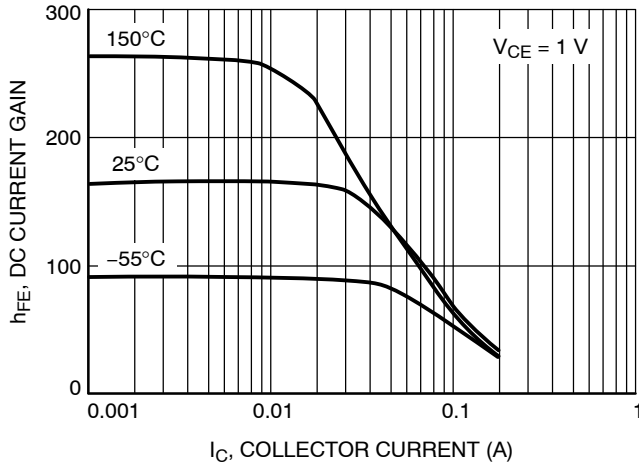


Figure 1. DC Current Gain vs. Collector Current

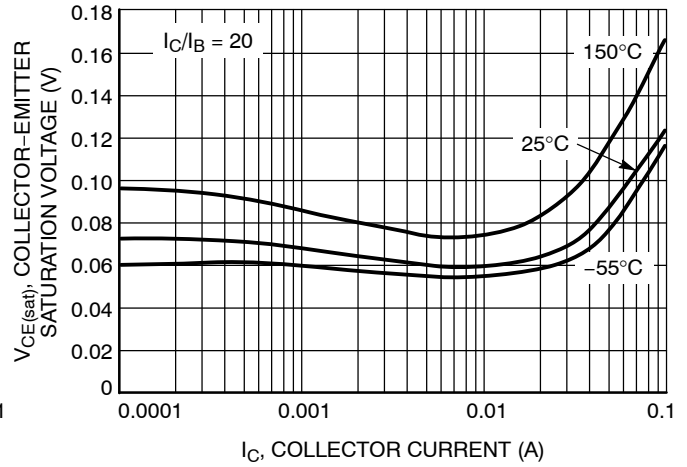


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

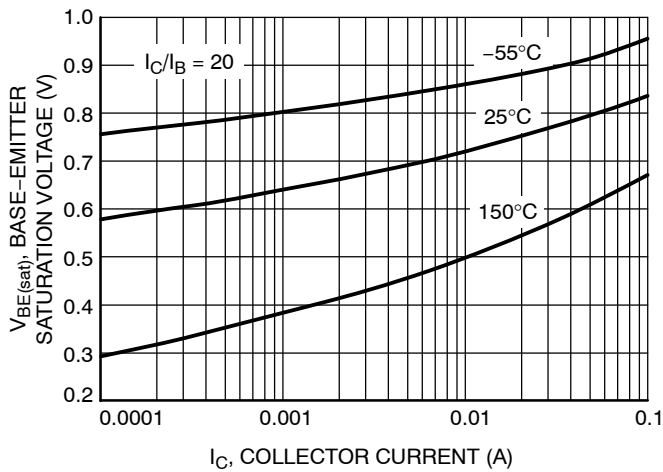


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

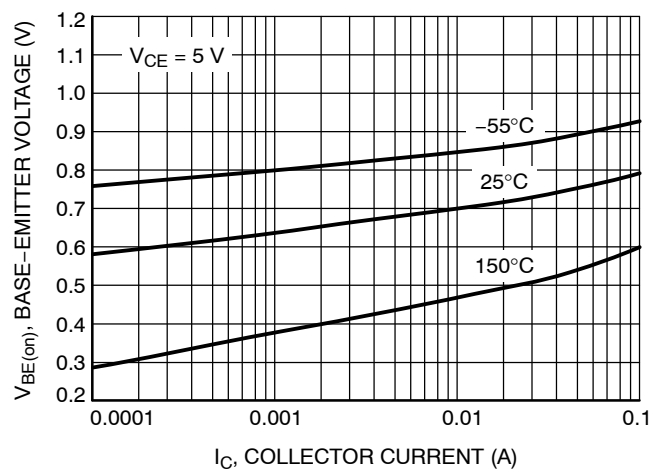


Figure 4. Base Emitter Voltage vs. Collector Current

BC846ALT1G Series

BC846A, BC847A, BC848A

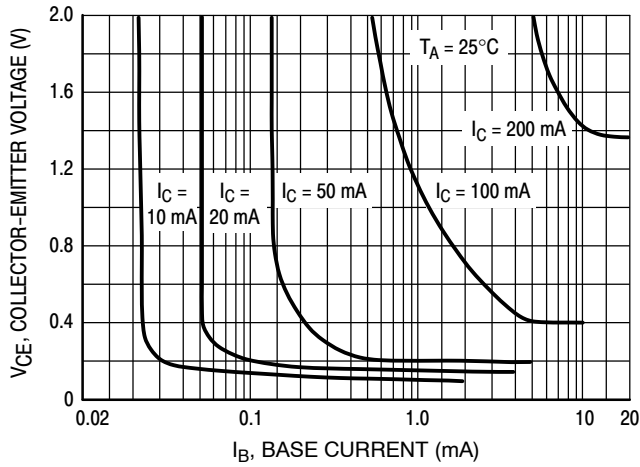


Figure 5. Collector Saturation Region

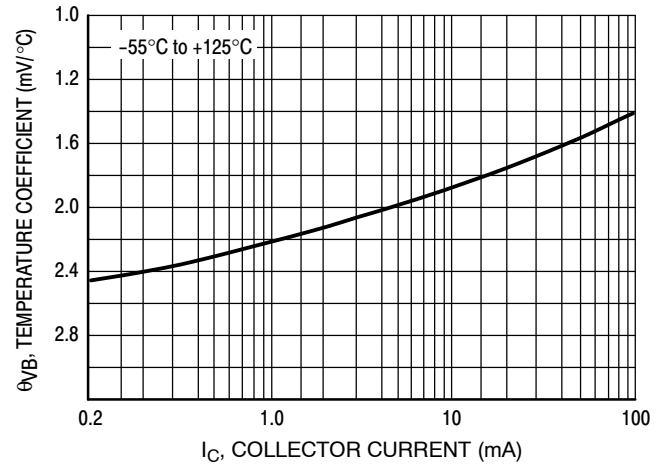


Figure 6. Base-Emitter Temperature Coefficient

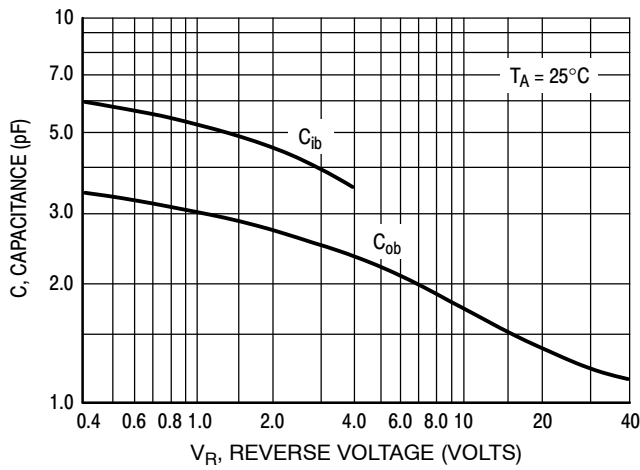


Figure 7. Capacitances

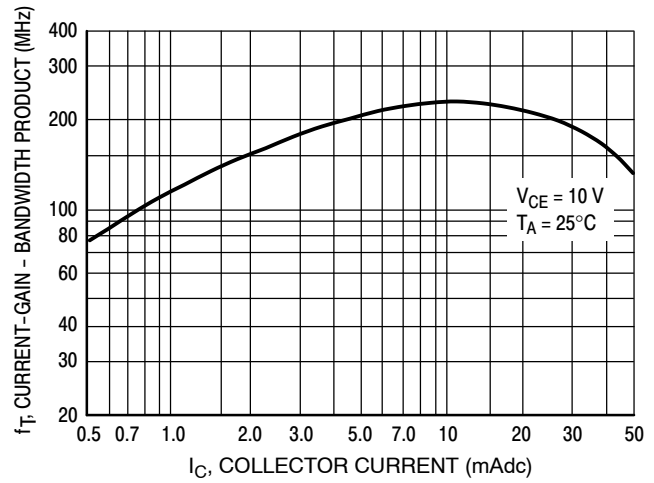


Figure 8. Current-Gain - Bandwidth Product

BC846ALT1G Series

BC846B

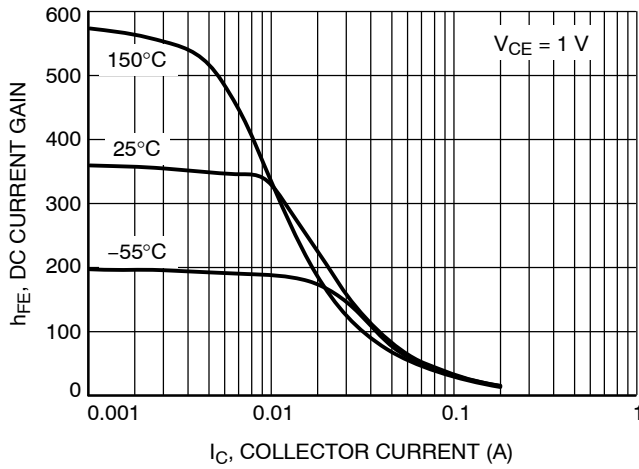


Figure 9. DC Current Gain vs. Collector Current

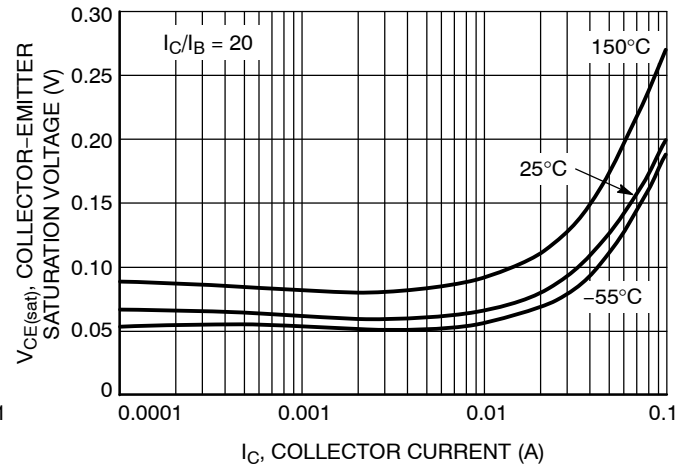


Figure 10. Collector Emitter Saturation Voltage vs. Collector Current

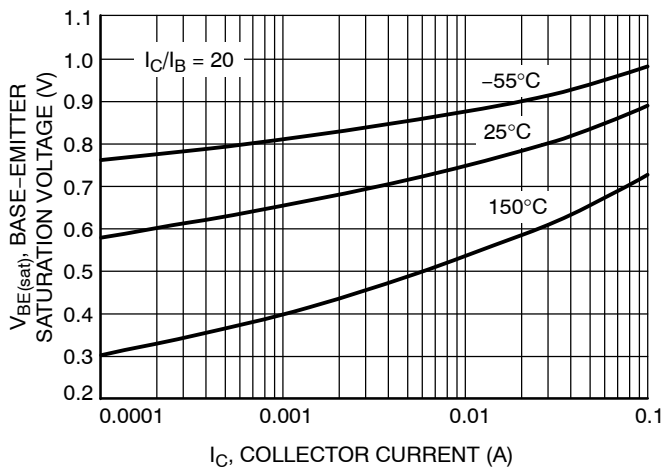


Figure 11. Base Emitter Saturation Voltage vs. Collector Current

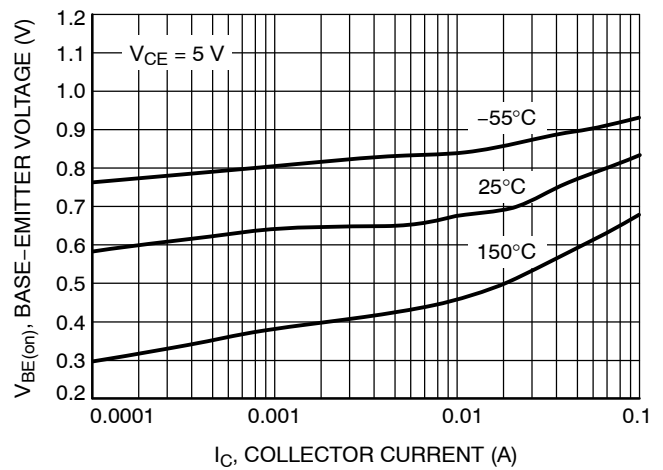


Figure 12. Base Emitter Voltage vs. Collector Current

BC846ALT1G Series

BC846B

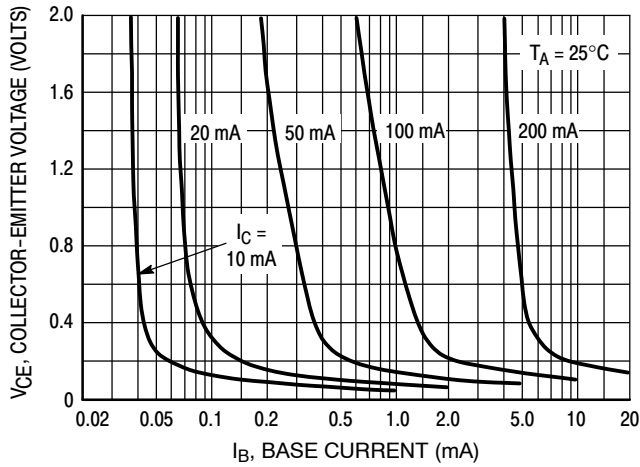


Figure 13. Collector Saturation Region

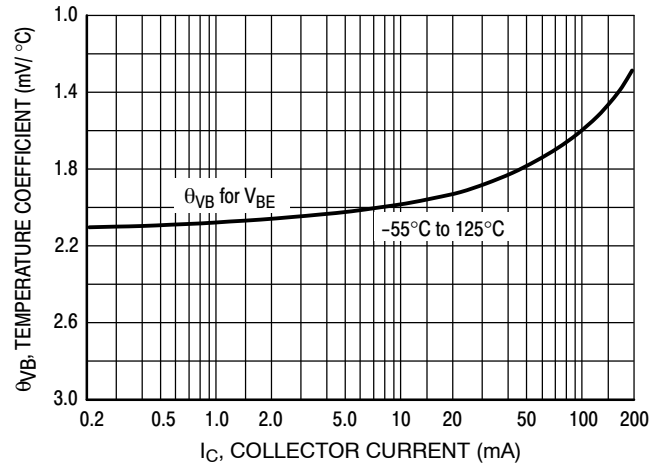


Figure 14. Base-Emitter Temperature Coefficient

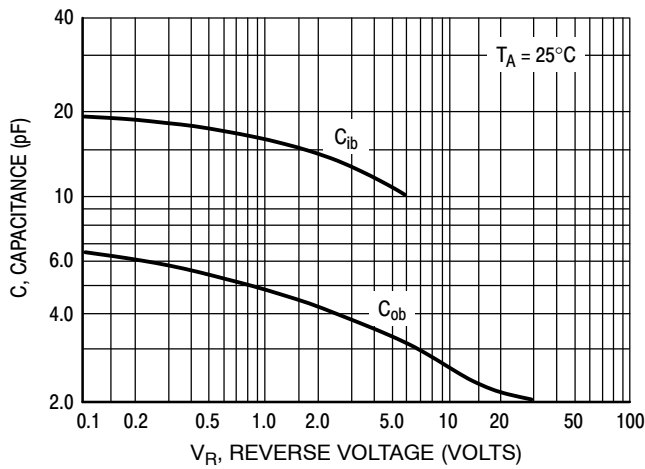


Figure 15. Capacitance

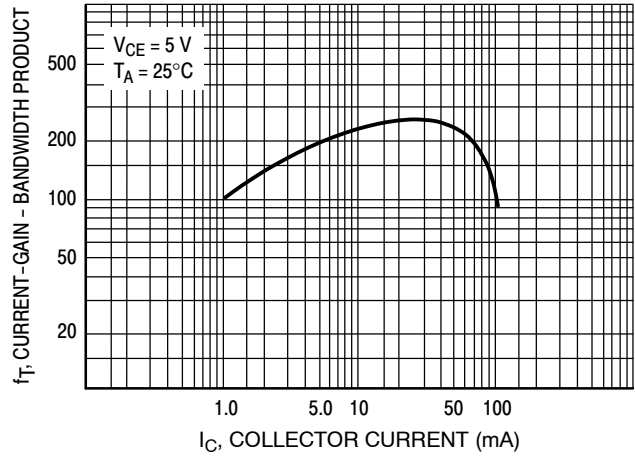


Figure 16. Current-Gain - Bandwidth Product

BC846ALT1G Series

BC847B, BC848B, BC849B, BC850B

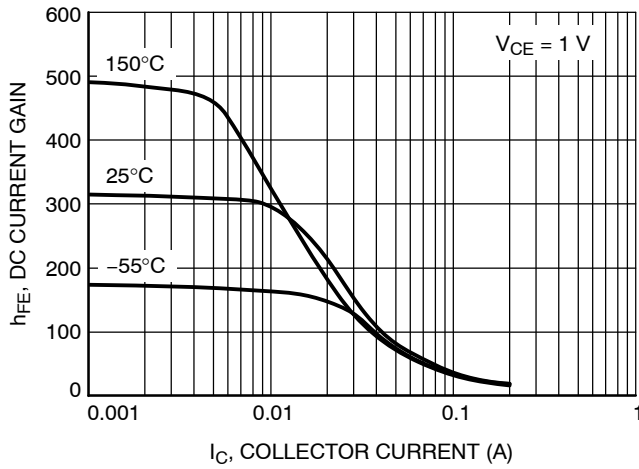


Figure 17. DC Current Gain vs. Collector Current

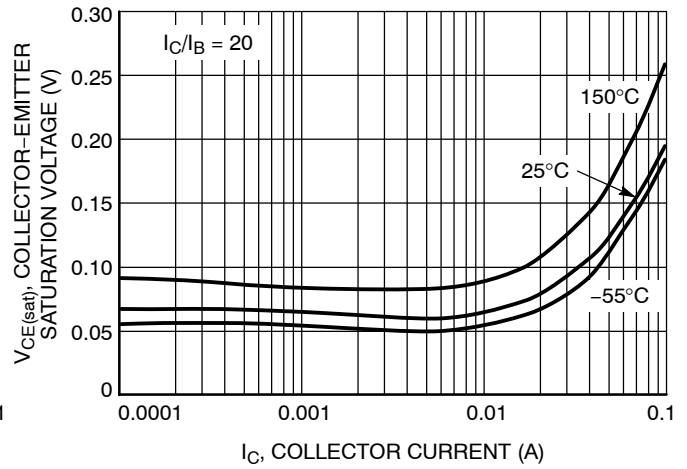


Figure 18. Collector Emitter Saturation Voltage vs. Collector Current

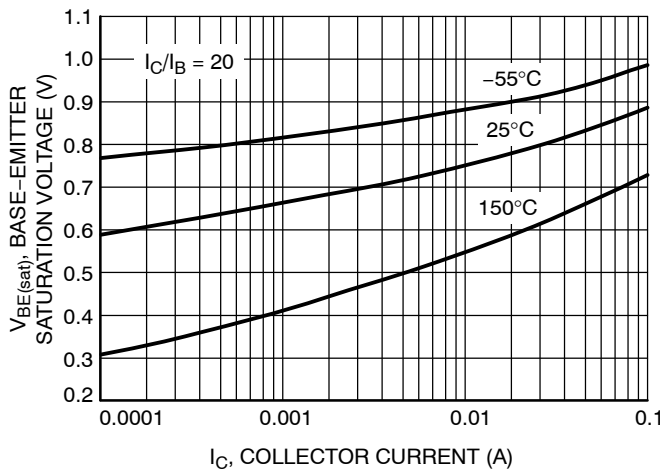


Figure 19. Base Emitter Saturation Voltage vs. Collector Current

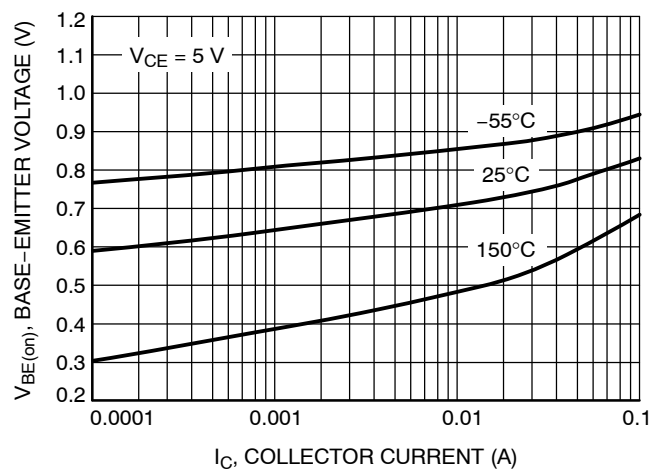


Figure 20. Base Emitter Voltage vs. Collector Current

BC846ALT1G Series

BC847B, BC848B, BC849B, BC850B

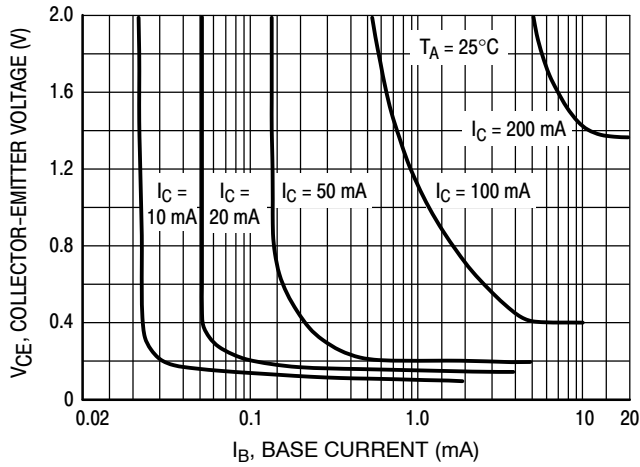


Figure 21. Collector Saturation Region

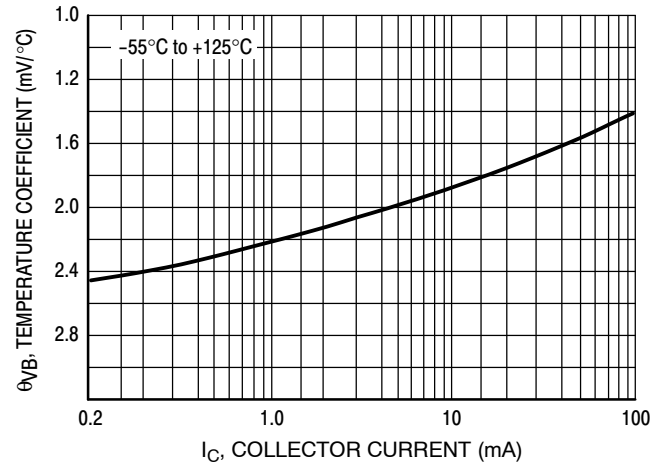


Figure 22. Base-Emitter Temperature Coefficient

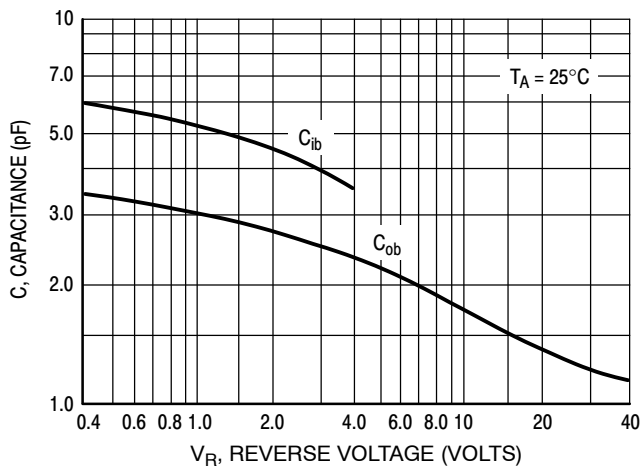


Figure 23. Capacitances

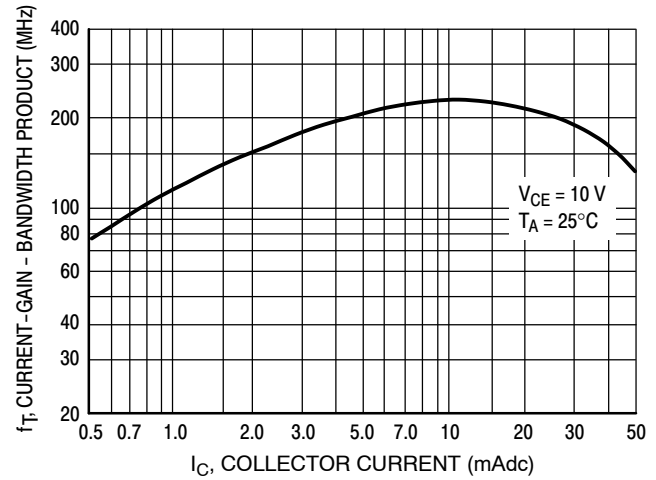


Figure 24. Current-Gain - Bandwidth Product

BC846ALT1G Series

BC847C, BC848C, BC849C, BC850C

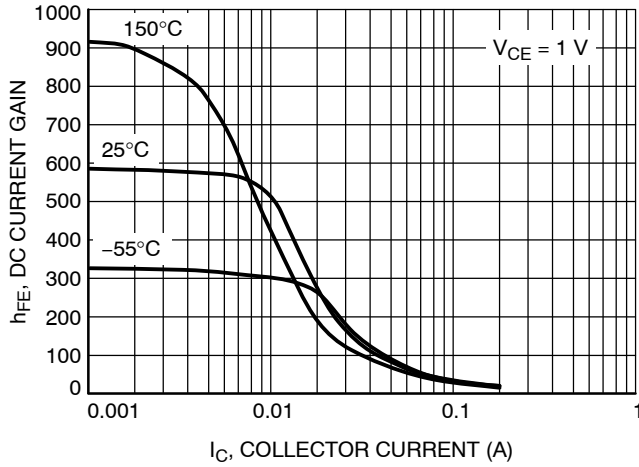


Figure 25. DC Current Gain vs. Collector Current

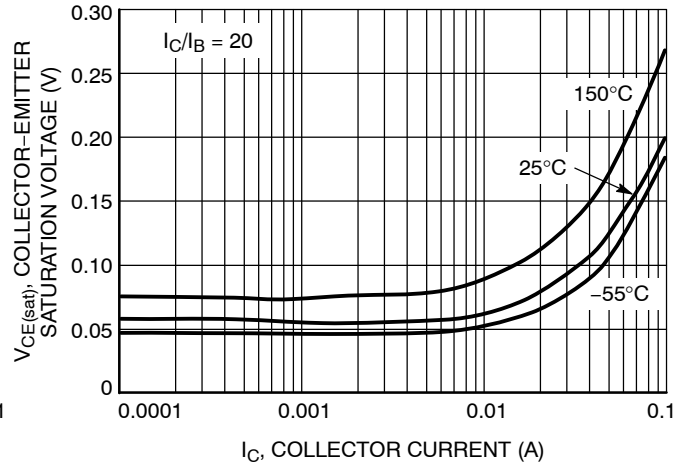


Figure 26. Collector Emitter Saturation Voltage vs. Collector Current

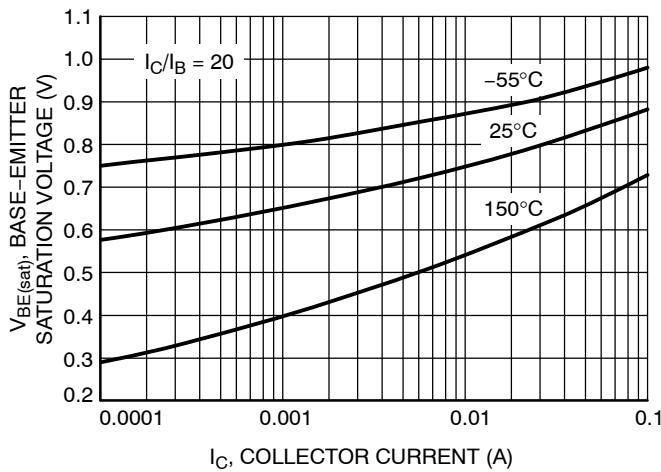


Figure 27. Base Emitter Saturation Voltage vs. Collector Current

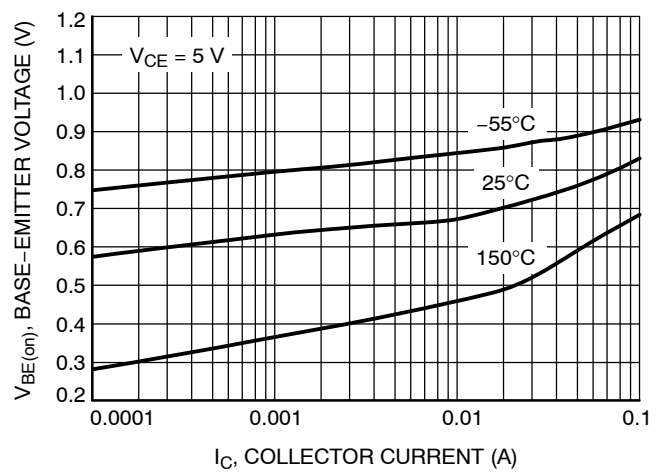


Figure 28. Base Emitter Voltage vs. Collector Current

BC846ALT1G Series

BC847C, BC848C, BC849C, BC850C

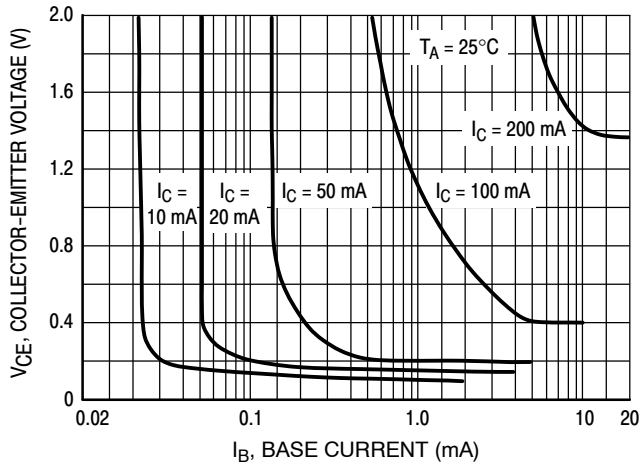


Figure 29. Collector Saturation Region

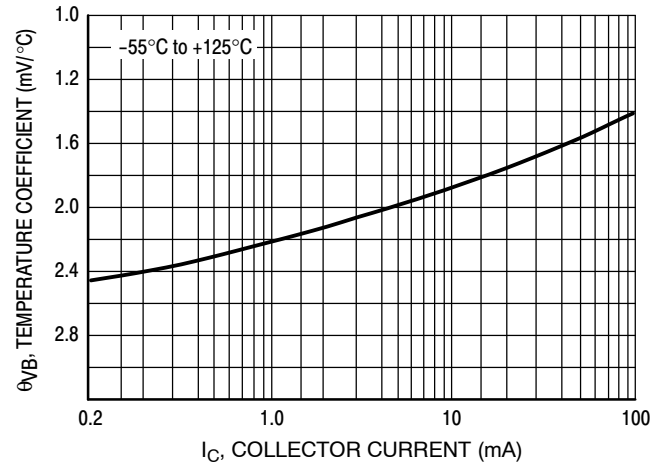


Figure 30. Base-Emitter Temperature Coefficient

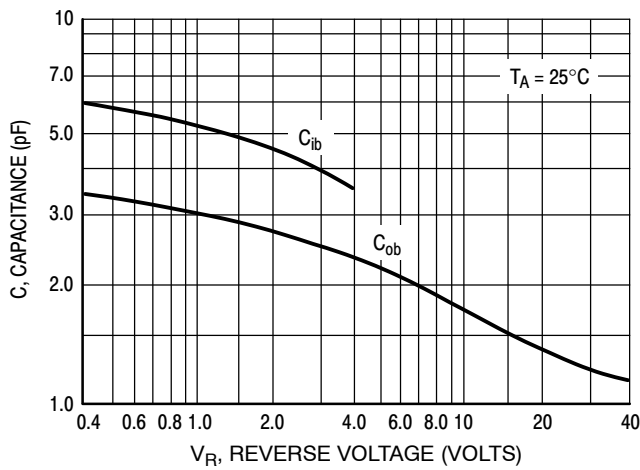


Figure 31. Capacitances

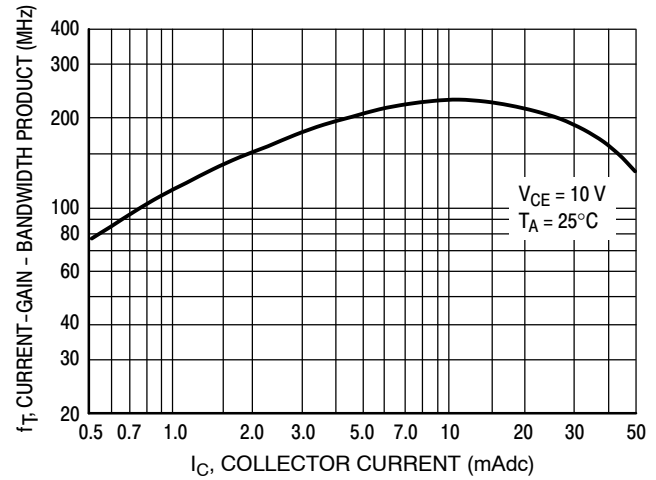
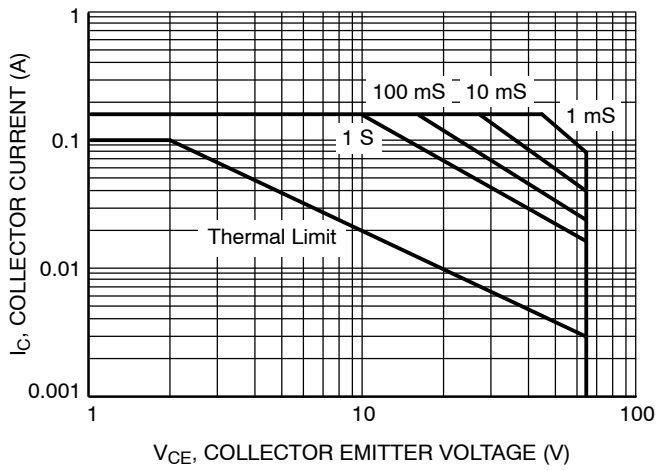
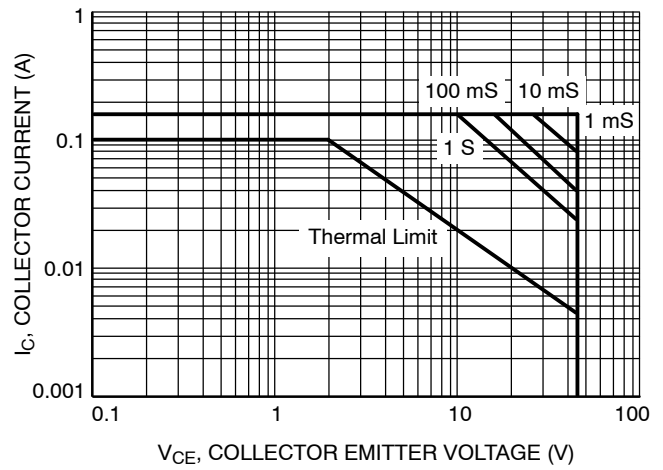


Figure 32. Current-Gain - Bandwidth Product

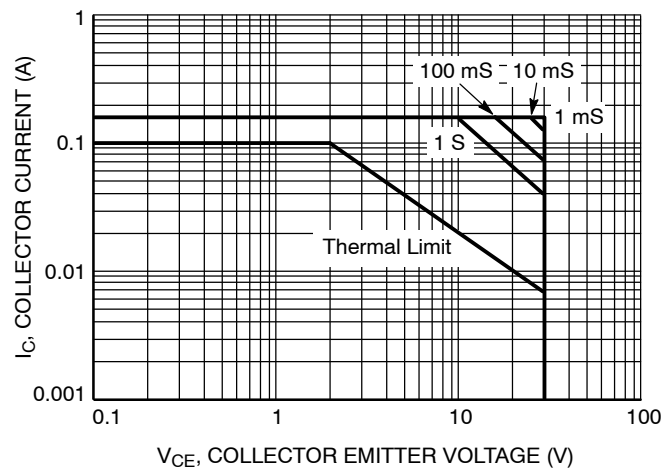
BC846ALT1G Series



**Figure 33. Safe Operating Area for
BC846A, BC846B**



**Figure 34. Safe Operating Area for
BC847A, BC847B, BC847C, BC850B, BC850C**



**Figure 35. Safe Operating Area for
BC848A, BC848B, BC848C, BC849B, BC849C**

BC846ALT1G Series

ORDERING INFORMATION

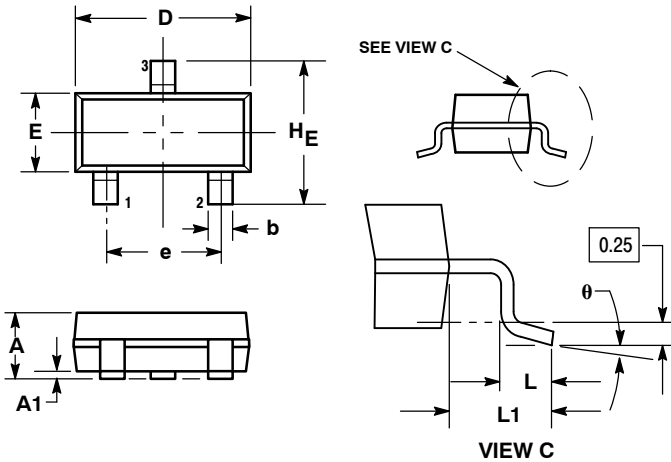
Device	Marking	Package	Shipping [†]
BC846ALT1G	1A	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BC846ALT3G		SOT-23 (Pb-Free)	10,000 / Tape & Reel
BC846BLT1G	1B	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BC846BLT3G		SOT-23 (Pb-Free)	10,000 / Tape & Reel
BC847ALT1G	1E	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BC847ALT3G		SOT-23 (Pb-Free)	10,000 / Tape & Reel
BC847BLT1G	1F	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BC847BLT3G		SOT-23 (Pb-Free)	10,000 / Tape & Reel
BC847CLT1G	1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BC847CLT3G		SOT-23 (Pb-Free)	10,000 / Tape & Reel
BC848ALT1G	1J	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BC848BLT1G	1K	SOT-23 (Pb-Free)	
BC848BLT3G		SOT-23 (Pb-Free)	10,000 / Tape & Reel
BC848CLT1G	1L	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BC848CLT3G		SOT-23 (Pb-Free)	10,000 / Tape & Reel
BC849BLT1G	2B	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BC849BLT3G		SOT-23 (Pb-Free)	10,000 / Tape & Reel
BC849CLT1G	2C	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BC849CLT3G		SOT-23 (Pb-Free)	10,000 / Tape & Reel
BC850BLT1G	2F	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BC850CLT1G	2G	SOT-23 (Pb-Free)	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BC846ALT1G Series

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AN



NOTES:

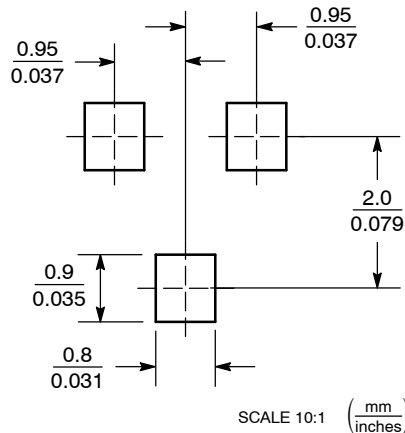
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

- PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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